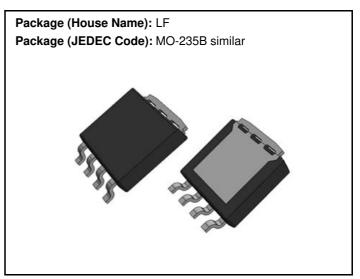
P32LF10SN

Power MOSFETs 100V, 32A, N-channel

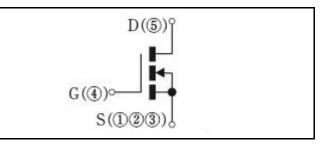
Feature

- N-channel
- Small SMD
- Large Current
- Low Ron
- 10V Gate Drive
- Low Capacitance
- Halogen free
- Pb free terminal
- RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 175	°C
Channel tempertature	Tch		-55 to 175	°C
Drain-source voltage	V _{DSS}		100	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		32	Α
Continuous drain current(Peak)	I _{DP}	Pulse width 10µs, duty=1/100	96	Α
Total power dissipation	P _T		168	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	25	Α
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	69	mJ

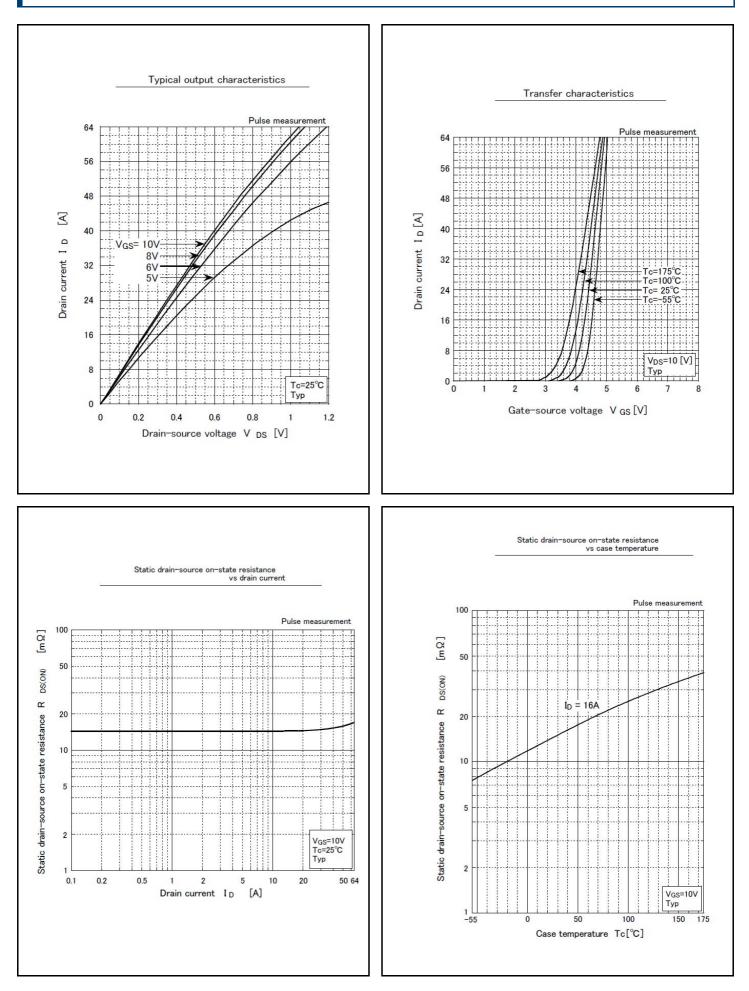
* : See the original Specifications

Electrical Characteristics (unless otherwise specified : Tc=25°C)

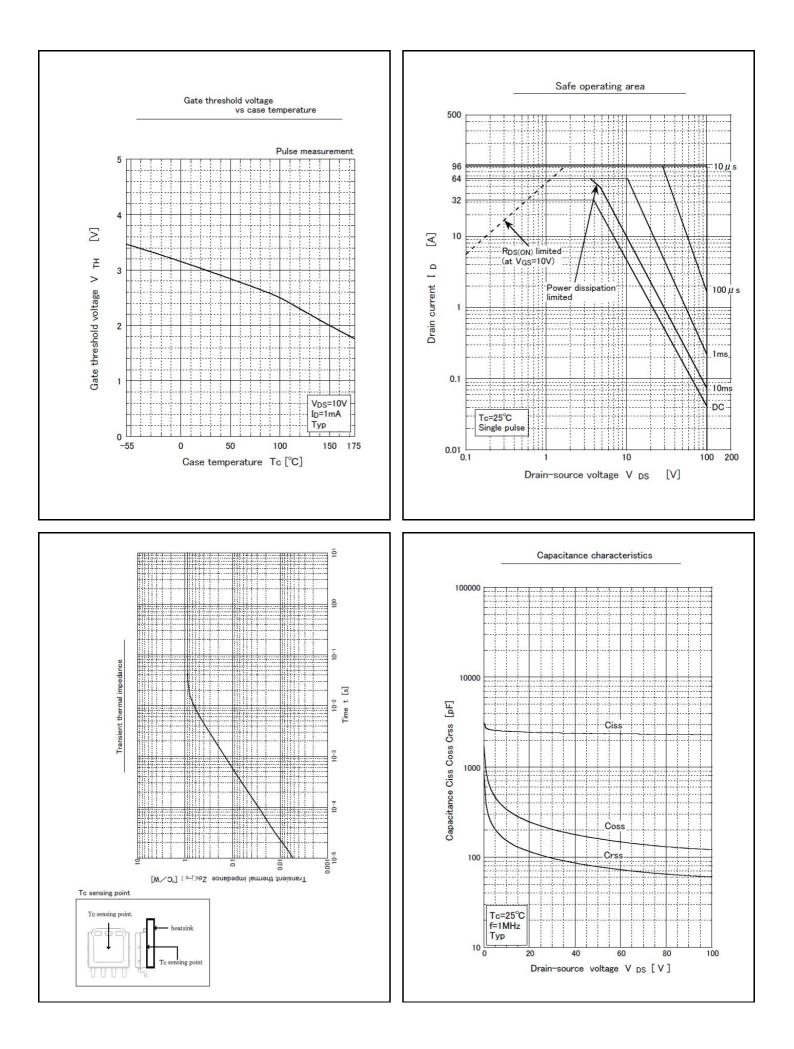
Item	Symbol	Conditions		Ratings		
			MIN	ТҮР	MAX	Unit
Drain-Source breakdown voltage	V _{(BR)DSS}	ID=1mA, VGS=0V	100			V
Zero gate voltage drain current	I _{DSS}	VDS=100V, VGS=0V			1	μA
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g _{fs}	ID=16A, VDS=10V	10			S
Static drain-source on-state resistance	R _{DS(ON)}	ID=16A, VGS=10V		0.0144	0.018	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	2	3	4	V
Source-drain diode forward voltage	V _{SD}	IS=32A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case, with heatsink			0.89	°C/W
Total gate charge	Qg	VDD=80V, VGS=10V, ID=32A		48		nC
Gate to source charge	Qgs	VDD=80V, VGS=10V, ID=32A		13.2		nC
Gate to drain charge	Qgd	VDD=80V, VGS=10V, ID=32A		16		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		2430		pF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		105		pF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		223		pF
Turn-on delay time	td(on)	ID=16A, RL=3.13Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		5.8		ns
Rise time	tr	ID=16A, RL=3.13Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		9		ns
Turn-off delay time	td(off)	ID=16A, RL=3.13Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		30		ns
Fall time	tf	ID=16A, RL=3.13Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		11		ns
Diode reverse recovery time	trr	IF=32A, VGS=0V, di/dt=100A/µs		54		ns
Diode reverse recovery charge	Qrr	IF=32A, VGS=0V, di/dt=100A/µs		105		nC

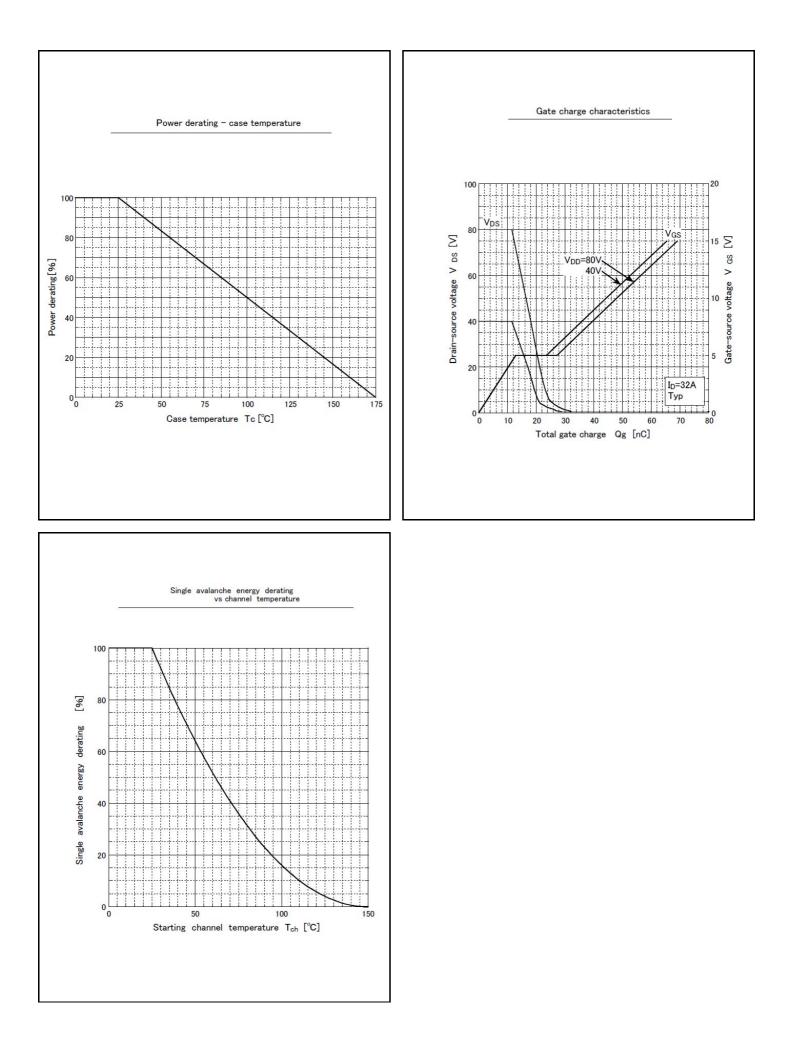
* : See the original Specifications

CHARACTERISTIC DIAGRAMS

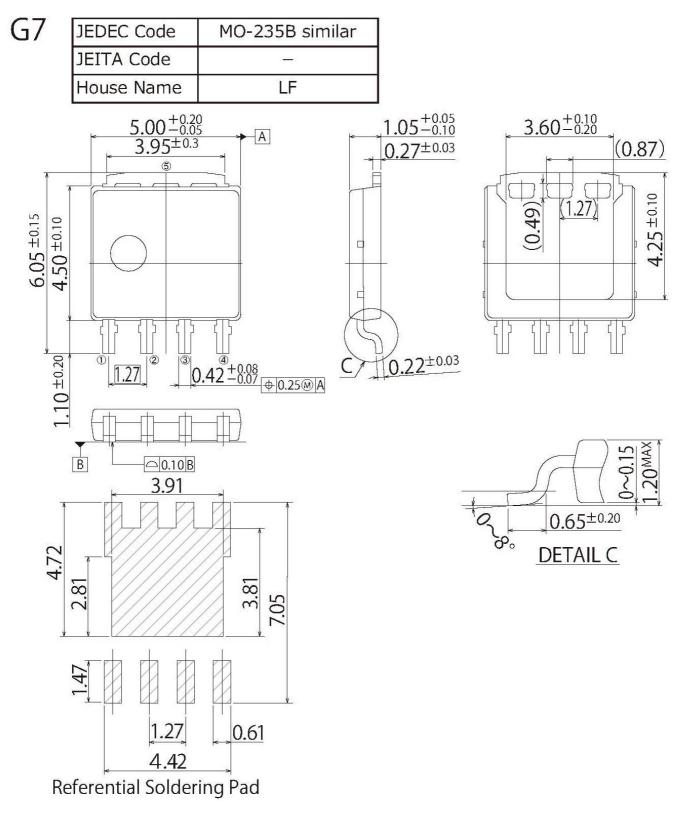


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unit:mm



Notes

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[Special applications]

Transportation equipment (vehicles, ships, etc.), trunk-line communication equipment, traffic signal control systems, antidisaster/crime systems, safety equipment, medical equipment, etc.

[Specific applications]

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